



WESTCODE SEMICONDUCTORS



Technical
Publication
TN029R

Issue 2
July 1985

Convertor Grade Stud-Base Thyristor Type N029R

30 amperes average: up to 1500 volts V_{RRM}

Ratings (Maximum values at 125°C T_j unless stated otherwise)

RATING	CONDITIONS	SYMBOL	
Average on-state current	Half sine wave. 96°C case temperature	$I_{T(AV)}$	30A
R.M.S on-state current		$I_{T(RMS)}$	48A
Continuous on-state current		I_T	48A
Peak one-cycle surge (non-repetitive) on-state current	10ms duration, 60% V_{RRM} re-applied	$I_{TSM(1)}$	500A
	10ms duration, $V_R \leq 10$ volts	$I_{TSM(2)}$	575A
	10ms duration, $V_R \leq 10$ volts	$I_{st}^{(2)}$	1653A ^{2s}
Maximum permissible surge energy	3ms duration, $V_R \leq 10$ volts	I_{st}	1174A ^{2s}
Peak forward gate current	Anode positive with respect to cathode	I_{FGM}	5A
Peak forward gate voltage	Anode positive with respect to cathode	V_{FGM}	20V
Peak reverse gate voltage		V_{RGM}	5V
Average gate power		P_G	1W
Peak gate power	100µs pulse width	P_{GM}	20W
Rate of rise of off-state voltage	To 80% V_{DRM} , gate open-circuit	dv/dt	*200V/µs
Rate of rise of on-state current (repetitive)	$\left\{ \begin{array}{l} T_{VJ} = 125^\circ\text{C}, I_G = 3 \times I_{GT}, dI_G/dt = 1\text{A}/\mu\text{s} \\ \text{Anode voltage} \leq 80\% V_{DRM} \end{array} \right\}$	$di/dt(1)$	200A/µs
Rate of rise on on-state current (non-repetitive)		$di/dt(2)$	400A/µs
Operating temperature range		T case	-40 +125°C
Storage temperature range		T _{stg}	-40 +150°C

Characteristics (Maximum values at 125°C T_j unless stated otherwise)

CHARACTERISTIC	CONDITIONS	SYMBOL	
Peak on-state voltage	At 94 A, I_{TM}	V_{TM}	1.93V
Forward conduction threshold voltage		V_O	1.17V
Forward conduction slope resistance		r	8.1mΩ
Repetitive peak off-state current	At V_{DRM}	I_{DRM}	5mA
Repetitive peak reverse current	At V_{RRM}	I_{RRM}	5mA
Maximum gate current required to fire all devices	$\left\{ \begin{array}{l} V_A = 6\text{V}, I_A = 500\text{mA at } 25^\circ\text{C } T_j \end{array} \right\}$	I_{GT}	100mA
Maximum gate voltage required to fire all devices		V_{GT}	3V
Maximum holding current		I_H	160mA
Maximum gate voltage which will not trigger any device		V_{GD}	0.25V
Thermal resistance, junction to case	DC and 180° sine wave	$R_{th(j-c)}$	0.55°C/W
for a device with a maximum forward volt drop characteristic	120° rectangular wave		0.69°C/W
Thermal resistance case to heatsink		$R_{th(c-hs)}$	0.1°C/W

VOLTAGE CODE		H02	H04	H06	H08	H10	H12	H15	
Repetitive peak voltages	V_{RRM} V_{DRM}								
Non-repetitive peak off-state voltage	V_{DSM}	200	400	600	800	1000	1200	1500	
Non-repetitive peak reverse blocking voltage	V_{RSM}	300	500	700	900	1100	1300	1600	

Ordering Information (Please quote device code as explained below – 8 digits)

N	0	2	9	R	● ● ●	
					Voltage code (see ratings)	Typical code: N029RH12 = 1200 V_{RRM} 1200V _{DRM} , 200 V/µs. dv/dt to 80% V_{DRM}

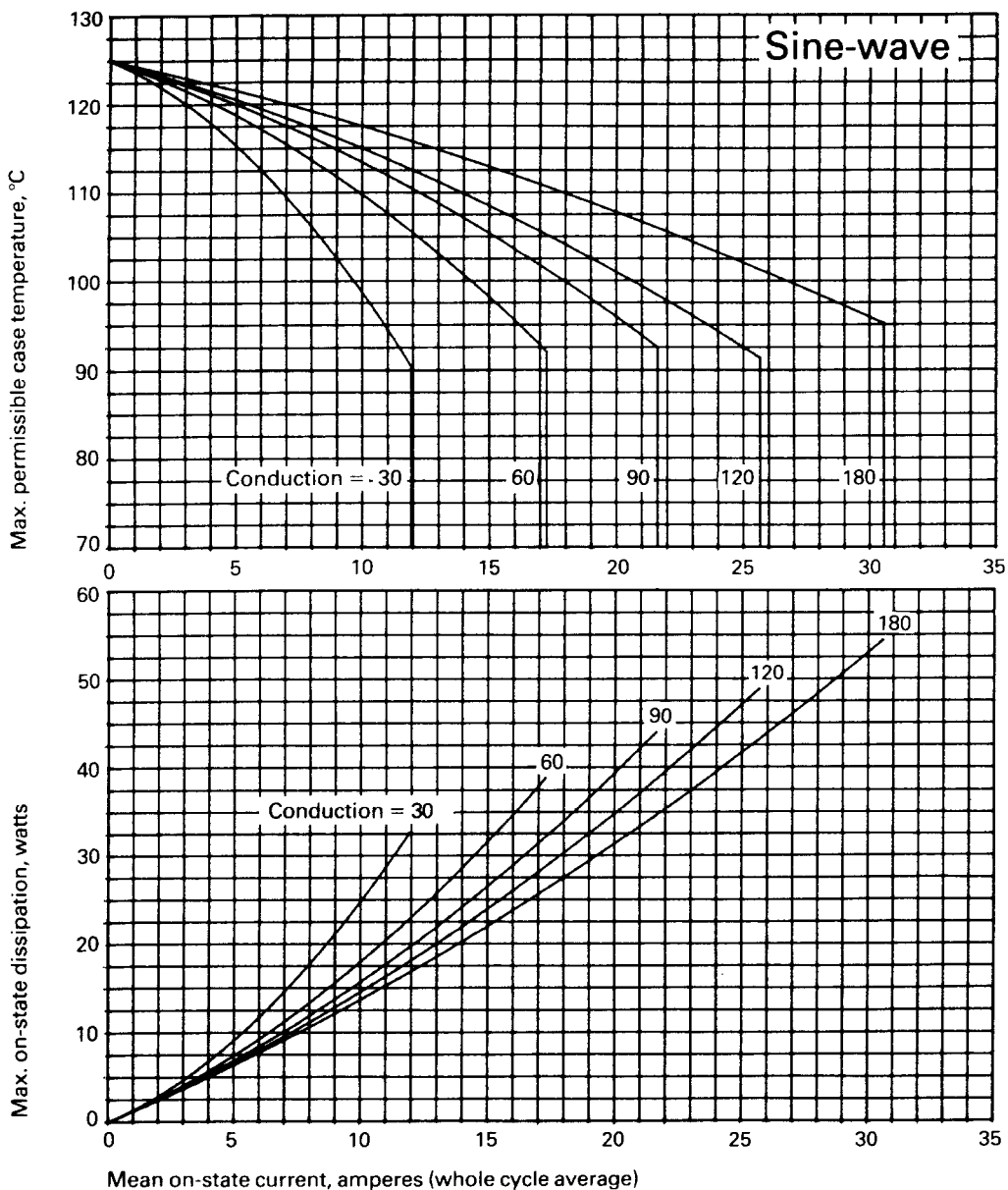


Figure 1 Dissipation and case temperature v. current

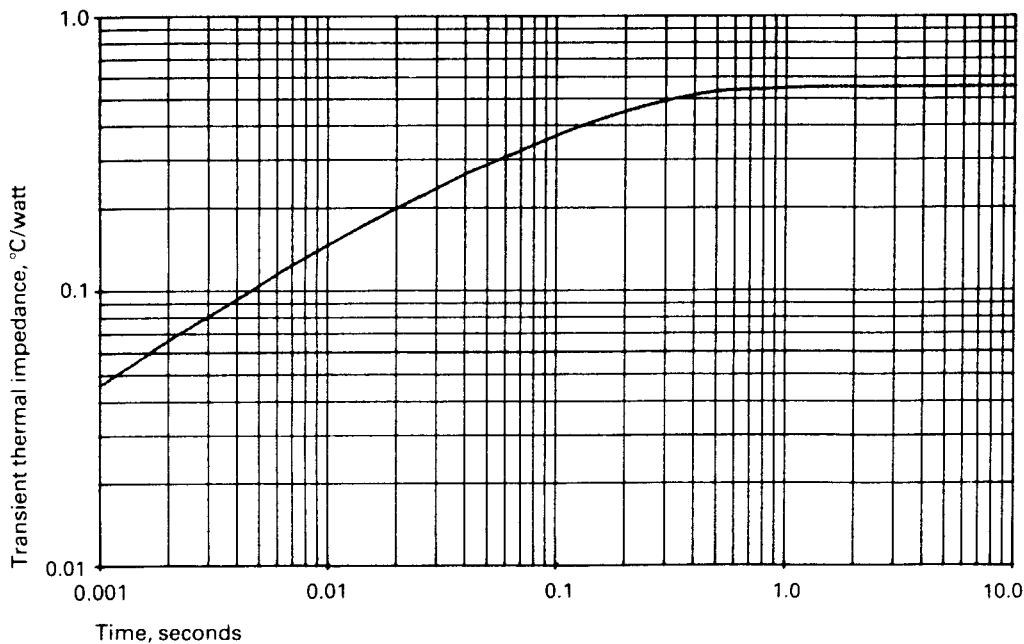


Figure 2 Junction to case thermal impedance

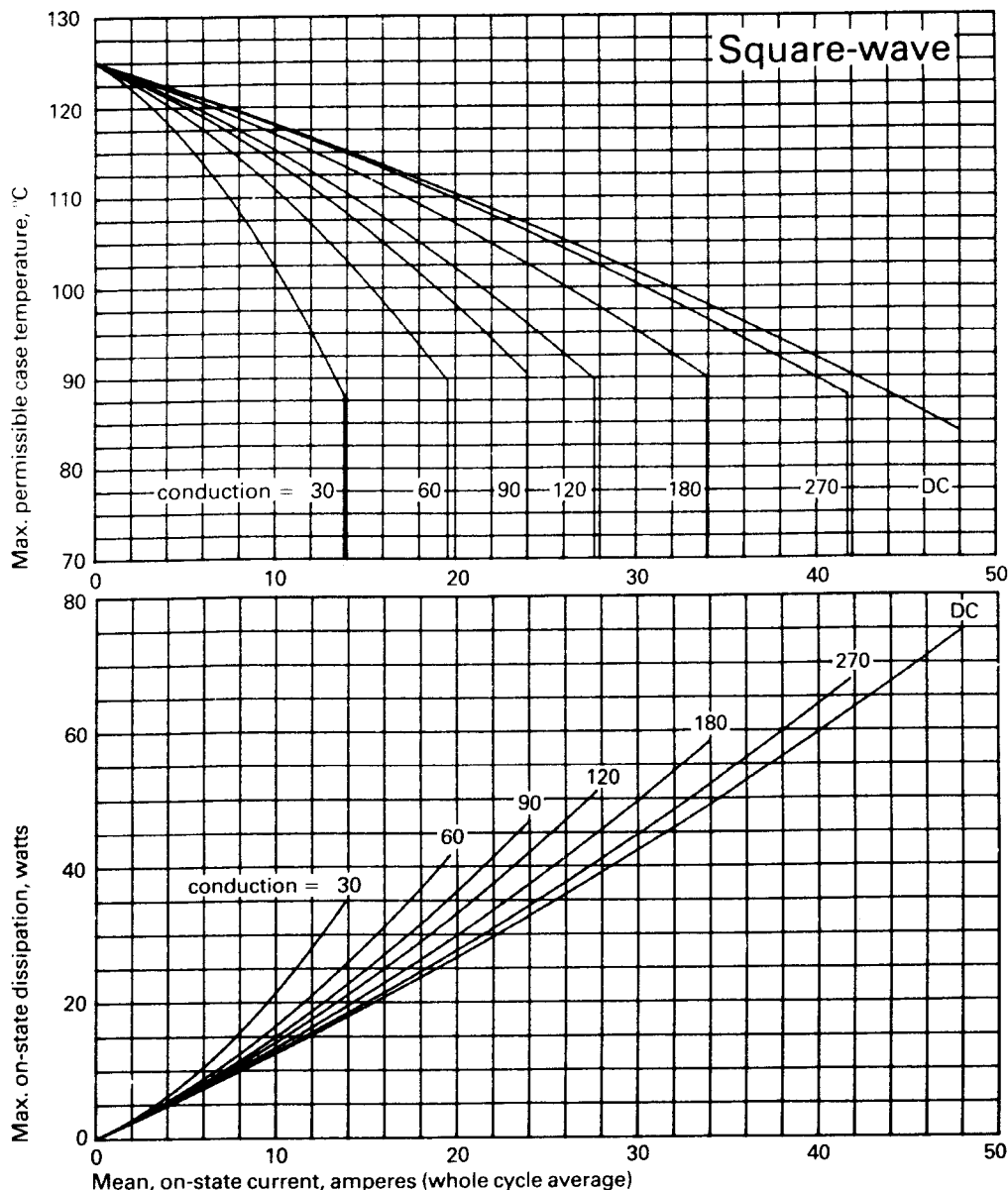


Figure 3 Dissipation and case temperature v. current

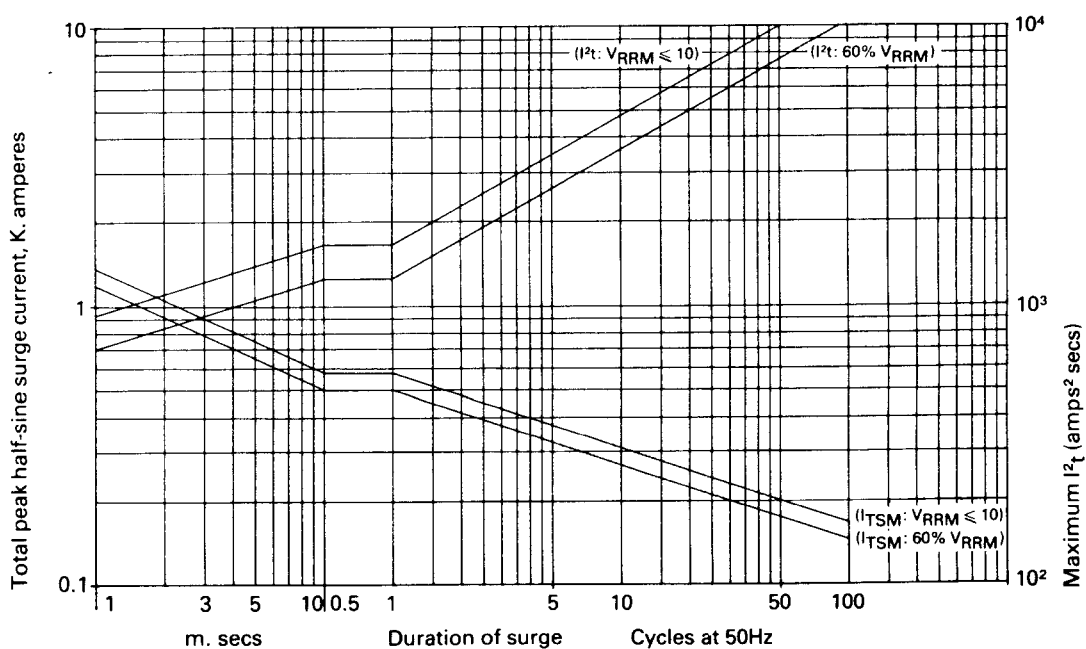


Figure 4 Max. non-repetitive surge current at initial junction temperature 125°C.

(gate may temporarily lose control of firing angle)

Note: This rating must not be interpreted as an intermittent rating

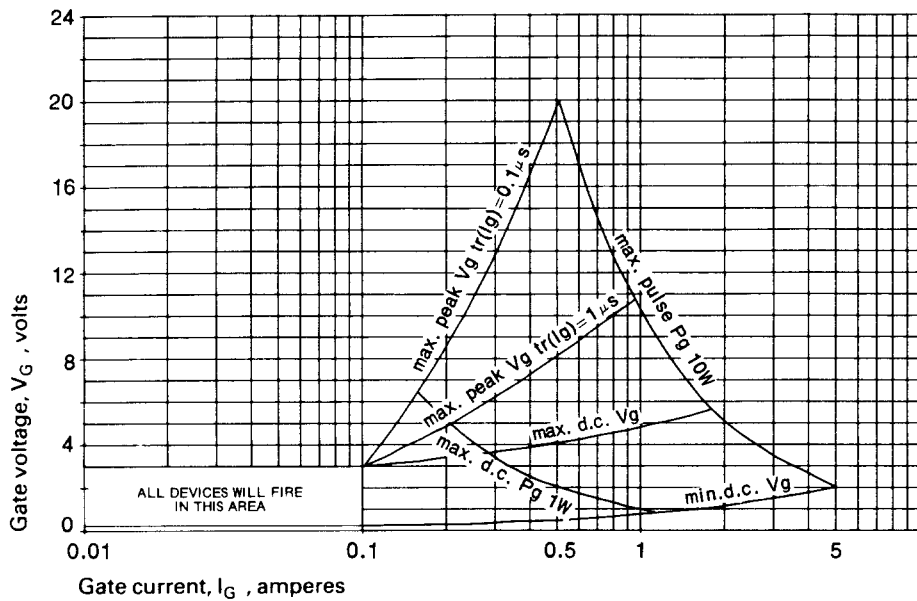


Figure 5 Gate characteristic at 25°C junction temperature

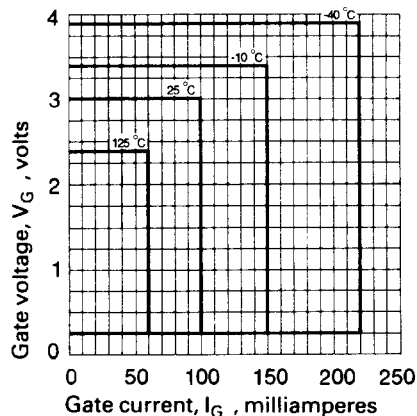


Figure 6 Gate triggering characteristics

Trigger points of all thyristors lie within the areas shown

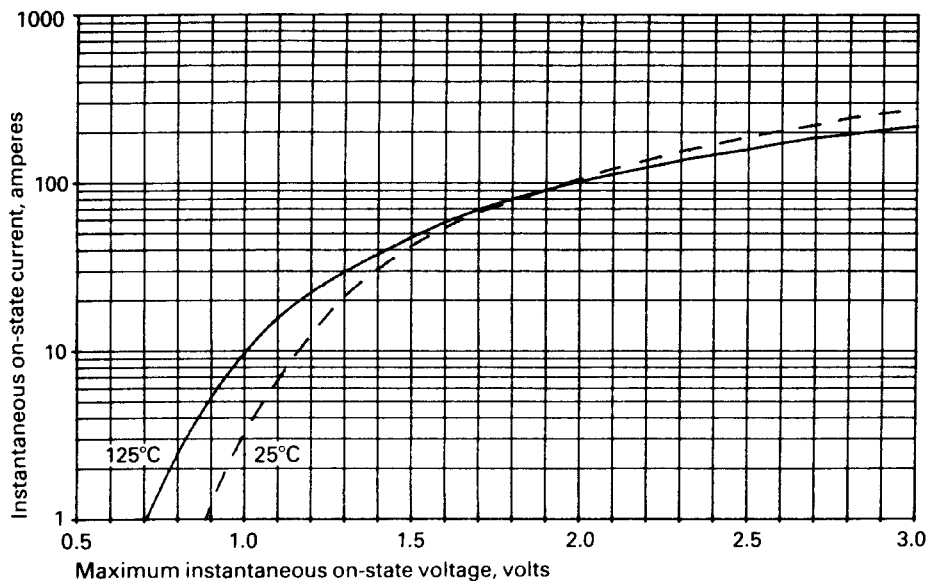
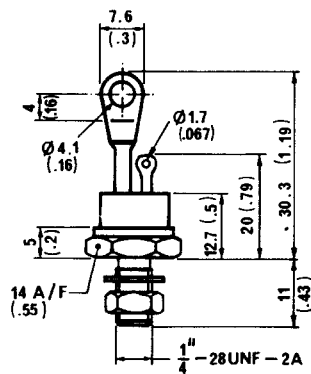


Figure 7 Limit on-state characteristic



Conforms to TO-48

dimensions in mm (inches)

Mounting torque: 0.41 – 0.48 KgM
threads not to be lubricated

Weight: 10 grams

In the interest of product improvement, Westcode reserves the right to change specifications at any time without notice.

WESTCODE SEMICONDUCTORS LTD

P.O. Box 57 Chippenham Wiltshire SN15 1JL England
Telephone Chippenham (0249) 654141 Telex 44751

HAWKER SIDDELEY

Westinghouse Brake and Signal Co. Ltd.